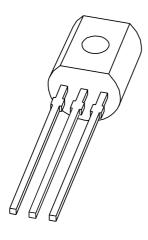
#### **DISCRETE SEMICONDUCTORS**

## DATA SHEET



# BS108 N-channel enhancement mode vertical D-MOS transistor

Product specification Supersedes data of 1997 Jun 17 2001 May 18





### N-channel enhancement mode vertical D-MOS transistor

**BS108** 

#### **FEATURES**

- Direct interface to C-MOS, TTL, etc.
- · High-speed switching
- No secondary breakdown.

#### **APPLICATIONS**

- Line current interruptor in telephone sets
- Applications in relay, high-speed and line transformer drivers.

#### **DESCRIPTION**

N-channel enhancement mode vertical D-MOS transistor in a SOT54 (TO-92) package.

#### **PINNING - SOT54**

PIN	DESCRIPTION
1	source
2	gate
3	drain

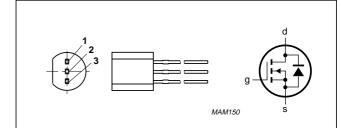


Fig.1 Simplified outline (SOT54; TO-92) and symbol.

#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>DS</sub>	drain-source voltage (DC)	200	V
$V_{GSth}$	gate-source threshold voltage	1.8	V
I <sub>D</sub>	drain current (DC)	300	mA
R <sub>DSon</sub>	drain-source on-state resistance	5	Ω

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>DS</sub>	drain-source voltage (DC)		_	200	V
$V_{GSO}$	gate-source voltage (DC)	open drain	_	±20	V
$I_D$	drain current (DC)		_	300	mA
I <sub>DM</sub>	peak drain current		_	1.2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	1	W
T <sub>stg</sub>	storage temperature		<b>-55</b>	+150	°C
Tj	junction temperature		_	150	°C

#### Note

1. Device mounted on a printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead minimum  $10 \times 10$  mm.

### N-channel enhancement mode vertical D-MOS transistor

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	125	K/W

#### Note

1. Device mounted on a printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead minimum  $10 \times 10$  mm.

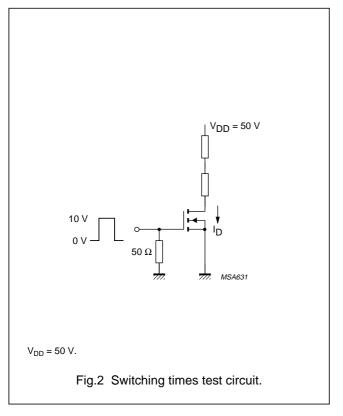
#### **CHARACTERISTICS**

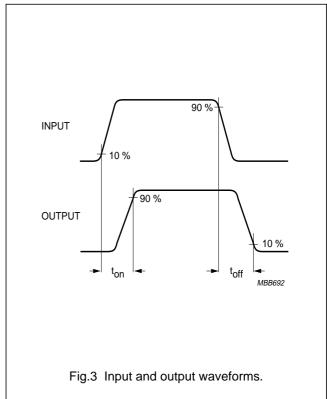
 $T_i = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 10  \mu A;  V_{GS} = 0$	200	_	_	٧
I <sub>DSS</sub>	drain-source leakage current	V <sub>DS</sub> = 160 V; V <sub>GS</sub> = 0	_	_	1	μΑ
I <sub>GSS</sub>	gate-source leakage current	$V_{GS} = \pm 20 \text{ V}; V_{DS} = 0$	_	_	±100	nA
$V_{GSth}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{GS} = V_{DS}$	0.4	_	1.8	V
R <sub>DSon</sub>	drain-source on-state resistance	$I_D = 100 \text{ mA}; V_{GS} = 2.8 \text{ V}$	_	2.7	5	Ω
Y <sub>fs</sub>	transfer admittance	$I_D = 300 \text{ mA}; V_{DS} = 25 \text{ V}$	200	600	_	mS
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0;$ f = 1 MHz	_	100	120	pF
C <sub>oss</sub>	output capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0;$ f = 1 MHz	_	20	30	pF
C <sub>rss</sub>	reverse transfer capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0;$ f = 1 MHz	_	10	15	pF
Switching ti	mes (see Figs 2 and 3)					
t <sub>on</sub>	turn-on time	$I_D = 250 \text{ mA}; V_{DD} = 50 \text{ V};$ $V_{GS} = 0 \text{ to } 10 \text{ V}$	-	6	10	ns
t <sub>off</sub>	turn-off time	$I_D$ = 250 mA; $V_{DD}$ = 50 V; $V_{GS}$ = 0 to 10 V	_	49	60	ns

### N-channel enhancement mode vertical D-MOS transistor

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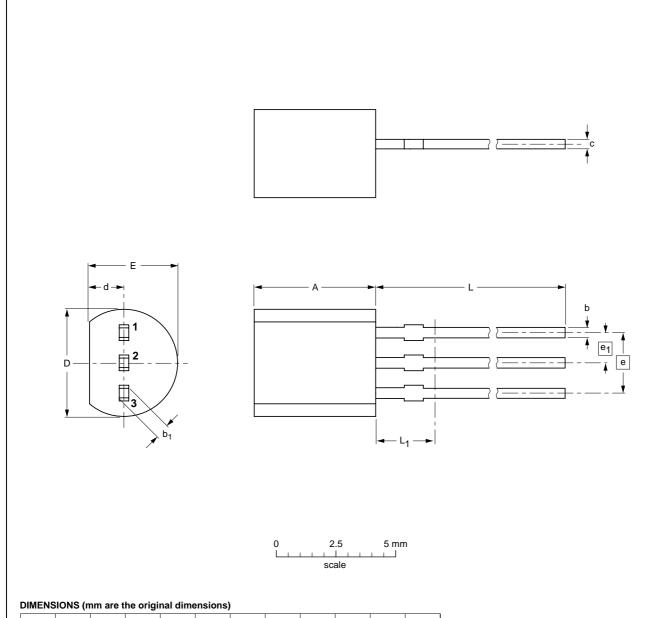
### N-channel enhancement mode vertical D-MOS transistor

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#### **PACKAGE OUTLINE**

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	A	b	b <sub>1</sub>	С	D	d	E	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup>
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

#### Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE	
SOT54		TO-92	SC-43		97-02-28	

### N-channel enhancement mode vertical D-MOS transistor

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DATA SHEET STATUS(1)	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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